MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TK32A12N1

1. Applications

- Switching Voltage Regulators

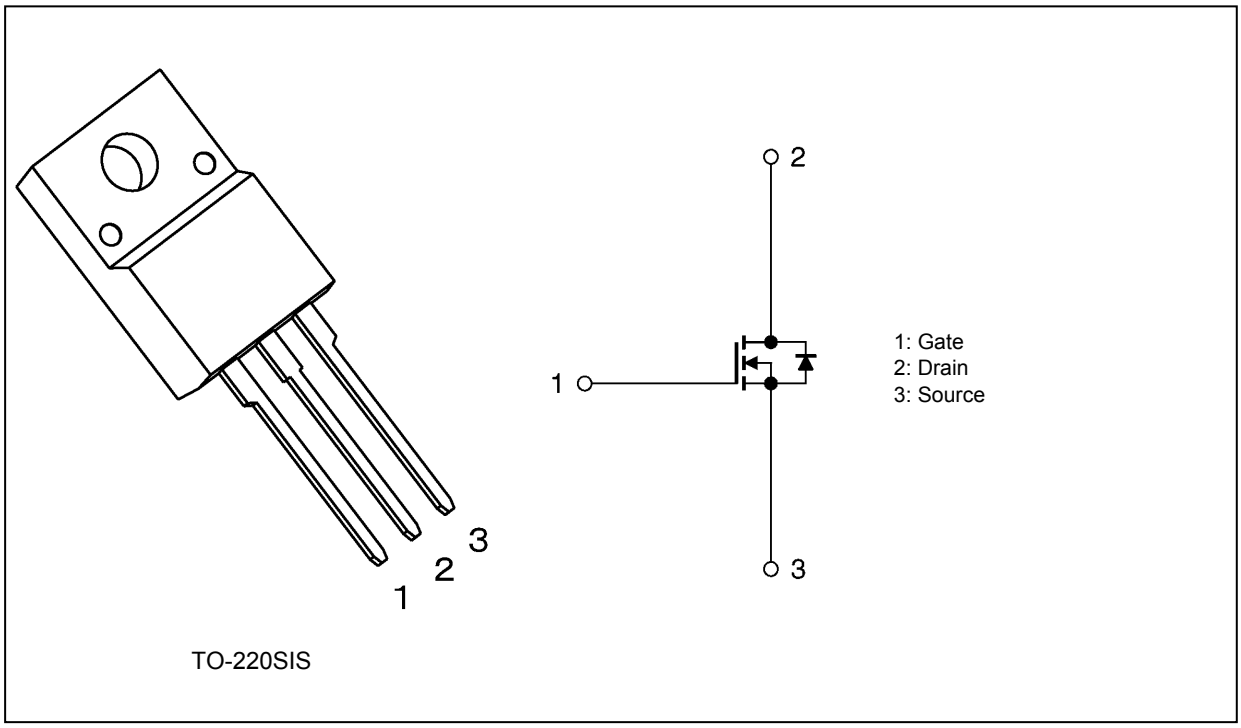
2. Features

(1) Low drain-source on-resistance: $R_{DS(ON)}$ = 11.0 mΩ (typ.) (V_{GS} = 10 V)

(2) Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 120 V)

(3) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 0.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	120	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I_D	60	A
Drain current (DC)	(T_c = 25°C)	(Note 1)	I_D	32	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I_{DP}	110	
Power dissipation	(T_c = 25°C)		P_D	30	W
Single-pulse avalanche energy		(Note 3)	E_{AS}	48	mJ
Avalanche current			I_{AR}	32	A
Channel temperature			T_{ch}	150	°C
Storage temperature			T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	4.16	°C/W
Channel-to-ambient thermal resistance	$R_{th(ch-a)}$	62.5	

Note 1: Ensure that the channel temperature does not exceed 150°C.
Note 2: Limited by silicon chip capability.
Note 3: V_{DD} = 80 V, T_{ch} = 25°C (initial), L = 46.1 μH, I_{AR} = 32 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

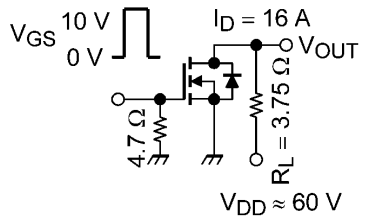
6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	—	—	±0.1	μA
Drain cut-off current	I_{DSS}	V_{DS} = 120 V, V_{GS} = 0 V	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	I_D = 10 mA, V_{GS} = 0 V	120	—	—	V
Drain-source breakdown voltage (Note 4)	$V_{(BR)DSX}$	I_D = 10 mA, V_{GS} = -20 V	90	—	—	
Gate threshold voltage	V_{th}	V_{DS} = 10 V, I_D = 0.5 mA	2.0	—	4.0	
Drain-source on-resistance	$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 16 A	—	11.0	13.8	mΩ

Note 4: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = 60 V, V_{GS} = 0 V, f = 1 MHz	—	2000	—	pF
Reverse transfer capacitance	C_{rss}		—	13	—	
Output capacitance	C_{oss}		—	330	—	
Gate resistance	r_g	—	—	1.9	—	Ω
Switching time (rise time)	t_r	See Figure 6.2.1	—	14	—	ns
Switching time (turn-on time)	t_{on}		—	33	—	
Switching time (fall time)	t_f		—	14	—	
Switching time (turn-off time)	t_{off}		—	43	—	



Duty ≤ 1%, t_w = 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} ≈ 96 V, V_{GS} = 10 V, I_D = 32 A	—	34	—	nC
Gate-source charge 1	Q_{gs1}		—	13	—	
Gate-drain charge	Q_{gd}		—	9.8	—	
Gate switch charge	Q_{SW}		—	15	—	

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC)	(Note 5)	I_{DR}	—	—	—	32	A
Reverse drain current (pulsed)	(Note 5)	I_{DRP}	—	—	—	110	
Diode forward voltage		V_{DSF}	I_{DR} = 32 A, V_{GS} = 0 V	—	—	-1.2	V
Reverse recovery time	(Note 6)	t_{rr}	I_{DR} = 32 A, V_{GS} = 0 V $-dI_{DR}/dt$ = 100 A/μs	—	73	—	ns
Reverse recovery charge	(Note 6)	Q_{rr}		—	160	—	nC

Note 5: Ensure that the channel temperature does not exceed 150°C.
Note 6: Ensure that V_{DS} peak does not exceed V_{DSS}.

8. Characteristics Curves (Note)

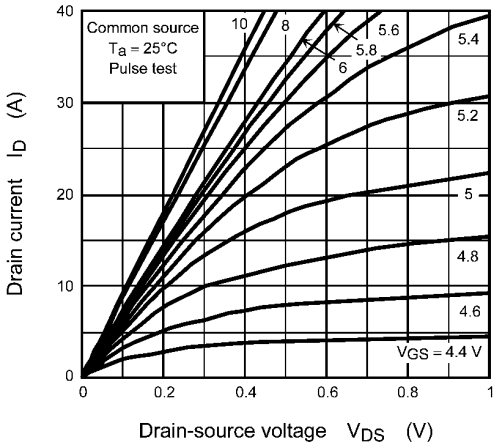


Fig. 8.1 I_D - V_{DS}

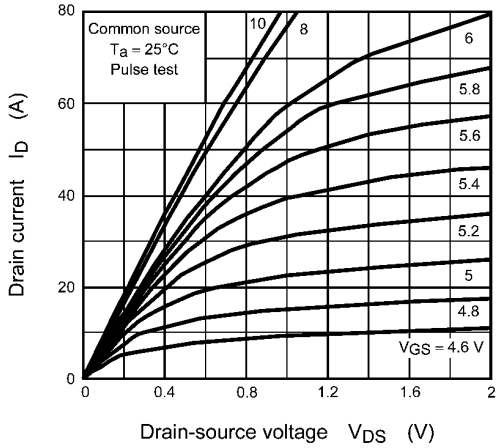


Fig. 8.2 I_D - V_{DS}

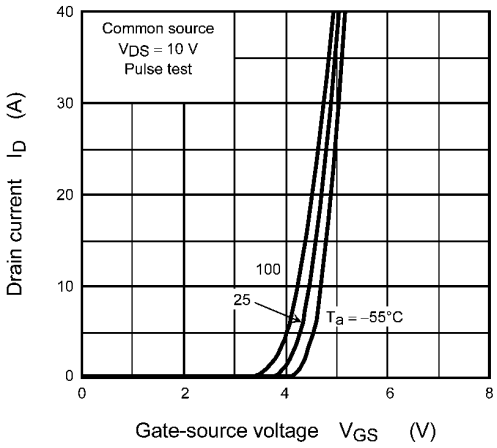


Fig. 8.3 I_D - V_{GS}

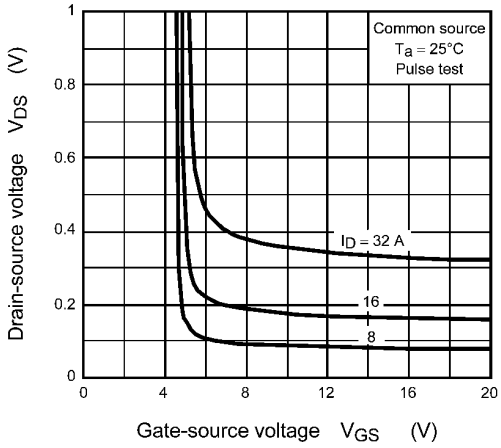


Fig. 8.4 V_{DS} - V_{GS}

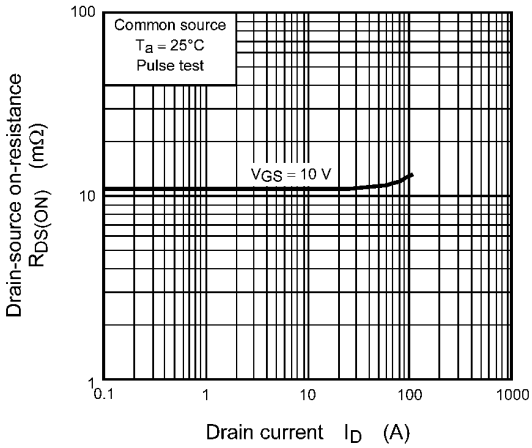


Fig. 8.5 $R_{DS(ON)}$ - I_D

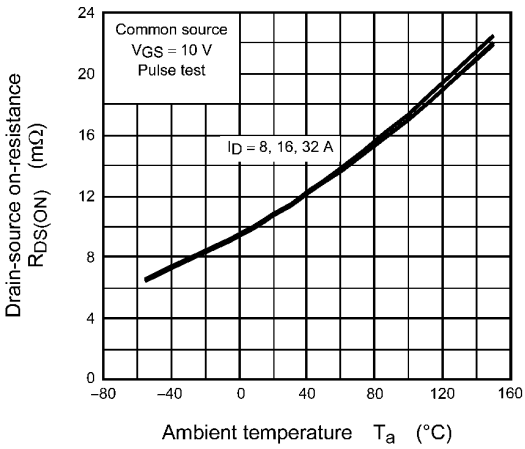


Fig. 8.6 $R_{DS(ON)}$ - T_a